



News Release / Presseinformation

Infineon Makes 2nd Generation of its ThinQ!TM Silicon Carbide Schottky Diodes Available in Fully Isolated TO-220 FullPAK Package

Neubiberg, Germany – May 5, 2010 – Infineon Technologies today announced the availability of its 2nd generation SiC (Silicon Carbide) Schottky diodes in the TO-220 FullPAK package. The new TO220 FullPak portfolio combines the high electrical performance standards of the 2nd generation ThinQ!TM SiC Schottky diodes with the advantages of a fully isolated package, including easier and more reliable mounting without having to use isolating bushing and foil.

Uniquely, the new TO220 FullPAK devices show a similar junction-to-heatsink thermal resistance as the standard non-isolated TO-220 devices. This is accomplished by using patented diffusion soldering technique from Infineon, which strongly reduces the “chip-to-leadframe” thermal resistance and effectively compensates for the FullPAK’s internal isolation layer. Infineon offers the 600V FullPAK portfolio in current ratings from 2A to 6A, making it the industry’s broadest portfolio of SiC diodes in this package type.

Silicon Carbide (SiC) is a revolutionary material for power semiconductors, with physical properties that far outperform Si power devices. Key features are a benchmark switching behavior, no reverse recovery, virtually no temperature influence on the switching behavior and a standard operating temperature of -55°C to 175°C. Main application areas for SiC Schottky diodes are active Power Factor Correction (PFC) in Switched Mode Power Supplies (SMPS) and other AC/DC and DC/DC power conversion applications such as solar inverters and motor drives. The FullPAK portfolio is perfectly suited for power supply application in flat panel displays (LCD/PDP) and computers.

Infineon was the world's first provider of SiC Schottky diodes, introducing its first products in 2001. During the last years, Infineon has made a number of significant improvements to its SiC Schottky diode technology in areas such as surge current

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stability, switching performance, product cost and packaging, extending the benefits of SiC technology. The SiC Schottky diodes are offered in 600V and 1200V.

Availability and Pricing

The full portfolio is released for production. Pricing is comparable to the equivalent parts in the TO220 package.

About Infineon

Infineon Technologies AG, Neubiberg, Germany, offers semiconductor and system solutions addressing three central challenges to modern society: energy efficiency, communications, and security. In the 2009 fiscal year (ending September), the company reported sales of Euro 3.03 billion with approximately 25,650 employees worldwide. With a global presence, Infineon operates through its subsidiaries in the U.S. from Milpitas, CA, in the Asia-Pacific region from Singapore, and in Japan from Tokyo. Infineon is listed on the Frankfurt Stock Exchange (ticker symbol: IFX) and in the USA on the over-the-counter market OTCQX International Premier (ticker symbol: IFNNY).

Further information is available at www.infineon.com

This news release is available online at www.infineon.com/press/

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